

10G 850nm VCSEL single and array chips RC0850-010MA-S(A)

Legal Disclaimer

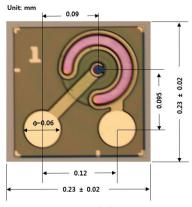
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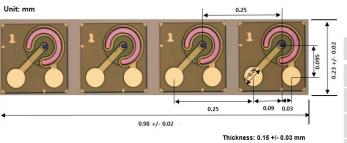
1. Specifications

RC0850-010MA-S



Thickness: 0.15 +/- 0.02 mm

RC0850-010MA-A



Electrical and optical characteristics

(T = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Note
Output power	P_{o}	1.5	1.8		mW	I = 6 mA
Threshold current	I_{th}		0.8	1.5	mA	
Operation voltage	V_{o}		2.1	2.3	V	I = 6 mA
Series resistance	R_s		50	70	Ω	I = 6 mA
Beam divergence	θ		28	35	degree	FW at 1/e ²
						I = 6 mA
Wavelength	λ	840	850	860	nm	I = 6 mA
Spectral width	Δλ			0.65	nm	I = 6 mA
Slope efficiency	η_{d}	0.20			mW/mA	
Peak temperature dependence	ΔΙ/ΔΤ		0.06		nm/°C	T = 0 to 70°C
3dB bandwidth	GHz	9	11			I = 6 mA

Absolute maximum ratings

(T = 25°C unless otherwise stated)

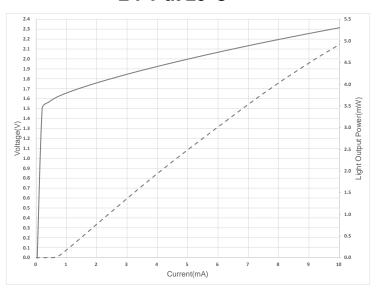
Parameter	Symbol	Rating	Unit	Notes
Forward current (Ta=25°C)	I _f	12	mA	
Reverse voltage	V_{r}	5	V	
Operating temperature range	T_{op}	0 ~ 80	°C	
Storage temperature	T_{stg}	-40 ~ 100	$^{\circ}$ C	
Reflow temperature	T_{ref}	260	℃	Max. 10sec 2mm from case

Notice

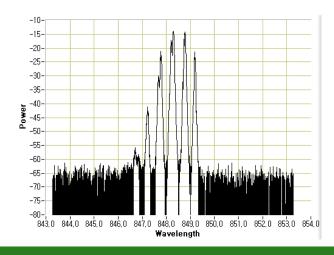
Conditions exceeding those listed may cause permanent damage to the device. Devices subjected to conditions beyond the limits specified for extended periods of time may adversely affect reliability.

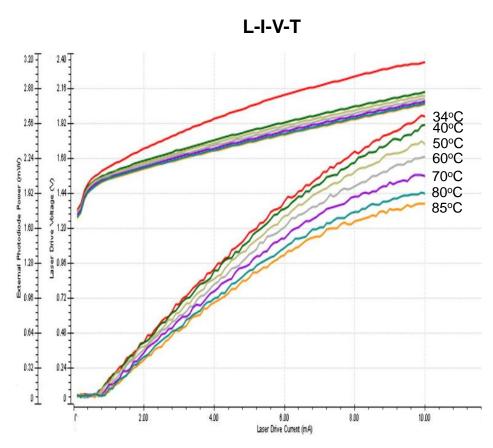
2. L-I-V & Spectrum

L-I-V at 25°C



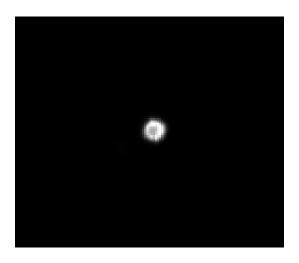
Spectrum at 25°C, 6mA



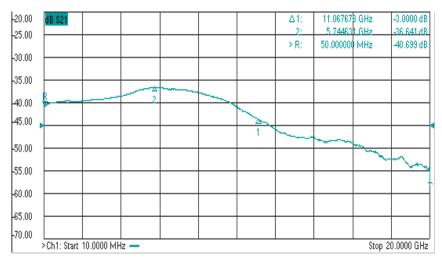


3. Near-field, f₃dB, Eye pattern

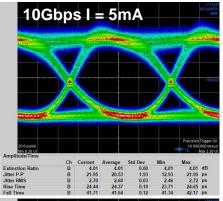
Near-field at 6mA

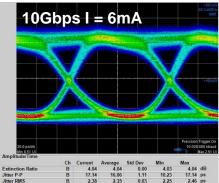


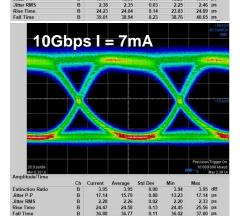
f₃dB at 6mA (25°C)



Eye pattern









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